

<b>Notice of References Cited</b>	Application/Control No. 10/579,036	Applicant(s)/Patent Under Reexamination KENJI KOHIRO	
	Examiner Felisa C. Hiteshew	Art Unit 1722	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
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**FOREIGN PATENT DOCUMENTS**

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**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	D. Keiper, et al., Metal organic vapor-phase epitaxy (MOVPE) growth of InP and InGaAs using tertiarybutylarsine (TBA) and tertiarybutylphosphine (TBP) in N <sub>2</sub> ambient. JOURNAL OF CRYSTAL GROWTH, Vol. 204, 1999, pages 256-262.
	V	
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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